

**APPARATUS AND PROCESS FOR PRODUCING
POLISHED SEMICONDUCTOR WAFERS**Abstract of the Disclosure

A process for forming a semiconductor wafer which is single side polished improves nanotopography and flatness of the polished wafer. The process reduces the effect of back side surface features, such as edge ring phenomena and back side laser marks, on nanotopography and local site flatness, thereby improving oxide layer uniformity for chemical/mechanical planarization (CMP) processing, and flatness on the polished front side of the wafer after polishing. The wafer is mounted on a polishing block by wax so as to minimize transfer of imperfections in the wax to the front side of the wafer. In particular, the wafer is retained in a centered position on the polishing block. Moreover, the wafer is mounted at atmospheric pressure while still removing air bubbles from the wax.

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